



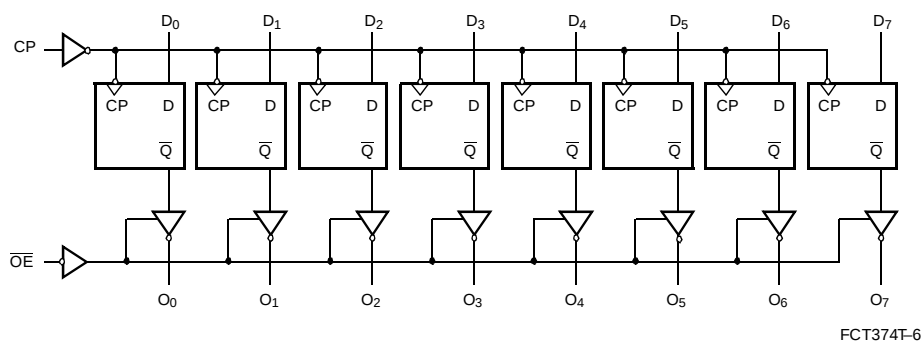
CY54/74FCT374T CY54/74FCT574T

8-Bit Registers

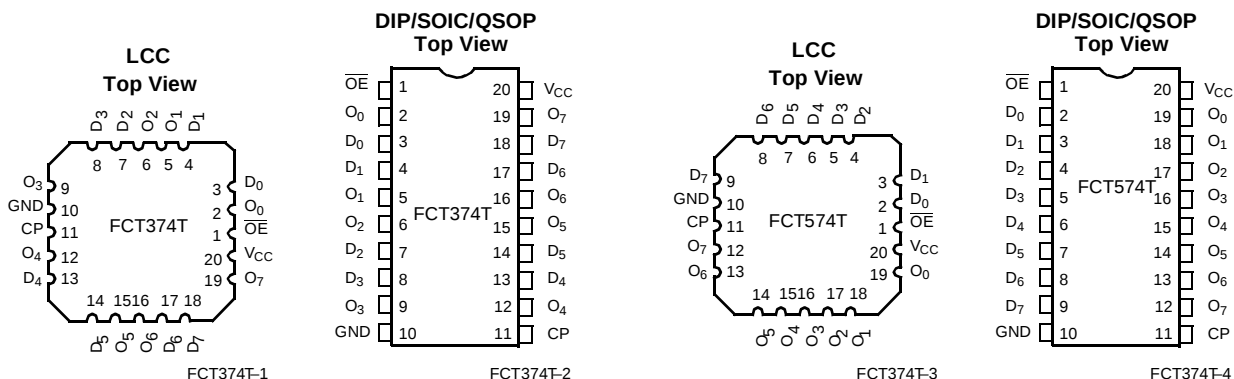
Features

- Function, pinout, and drive compatible with FCT and F logic
- FCT-C speed at 5.2 ns max. (Com'l)
FCT-A speed at 6.5 ns max. (Com'l)
- Reduced V_{OH} (typically = 3.3V) versions of equivalent FCT functions
- Edge-rate control circuitry for significantly improved noise characteristics
- Power-off disable feature
- Matched rise and fall times
- Fully compatible with TTL input and output logic levels
- ESD > 2000V
- Extended commercial range of -40°C to $+85^{\circ}\text{C}$
- Sink Current 64 mA (Com'l), 32 mA (Mil)
 Source Current 32 mA (Com'l), 12 mA (Mil)
- Edge-triggered D-type inputs
- 250 MHz typical toggle rate

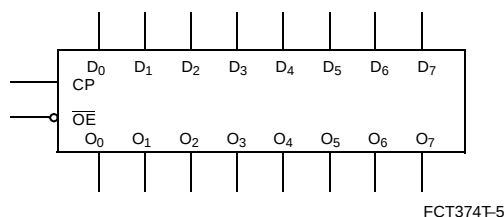
Logic Block Diagram



Pin Configurations



Logic Symbol



Functional Description

The FCT374T and FCT574T are high-speed low-power octal D-type flip-flops featuring separate D-type inputs for each flip-flop. Both devices have three-state outputs for bus oriented applications. A buffered clock (CP) and output enable ($\overline{OE}$) are common to all flip-flops. The FCT574T is identical to FCT374T except for flow-through pinout to simplify board design. The eight flip-flops contained in the FCT374T and FCT574T will store the state of their individual D inputs that meet the set-up and hold time requirements on the LOW-to-HIGH clock (CP) transition. When $\overline{OE}$ is LOW, the contents of the eight flip-flops are available at the outputs. When $\overline{OE}$ is HIGH, the outputs will be in the high-impedance state. The state of output enable does not affect the state of the flip-flops.

The outputs are designed with a power-off disable feature to allow for live insertion of boards.

Function Table^[1]

Inputs			Outputs
D	CP	OE	O
H	$\downarrow$	L	H
L	$\downarrow$	L	L
X	X	H	Z

Maximum Ratings^[2, 3]

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature	-65°C to +150°C
Ambient Temperature with Power Applied	-65°C to +135°C
Supply Voltage to Ground Potential	-0.5V to +7.0V
DC Input Voltage	-0.5V to +7.0V
DC Output Voltage	-0.5V to +7.0V
DC Output Current (Maximum Sink Current/Pin)	120 mA
Power Dissipation.....	0.5W
Static Discharge Voltage	>2001V (per MIL-STD-883, Method 3015)

Operating Range

Range	Range	Ambient Temperature	V _{CC}
Commercial	DT	0°C to +70°C	5V ± 5%
Commercial	T, AT, CT	-40°C to +85°C	5V ± 5%
Military ^[4]	All	-55°C to +125°C	5V ± 10%

Electrical Characteristics Over the Operating Range

Parameter	Description	Test Conditions		Min.	Typ. ^[5]	Max.	Unit
V _{OH}	Output HIGH Voltage	V _{CC} =Min., I _{OH} =−32 mA	Com'l	2.0			V
		V _{CC} =Min., I _{OH} =−15 mA	Com'l	2.4	3.3		V
		V _{CC} =Min., I _{OH} =−12 mA	Mil	2.4	3.3		V
V _{OL}	Output LOW Voltage	V _{CC} =Min., I _{OL} =64 mA	Com'l		0.3	0.55	V
		V _{CC} =Min., I _{OL} =32 mA	Mil		0.3	0.55	V
V _{IH}	Input HIGH Voltage			2.0			V
V _{IL}	Input LOW Voltage					0.8	V
V _H	Hysteresis ^[6]	All inputs			0.2		V
V _{IK}	Input Clamp Diode Voltage	V _{CC} =Min., I _{IN} =−18 mA			−0.7	−1.2	V
I _I	Input HIGH Current	V _{CC} =Max., V _{IN} =V _{CC}				5	μA
I _{IH}	Input HIGH Current	V _{CC} =Max., V _{IN} =2.7V				±1	μA
I _{IL}	Input LOW Current	V _{CC} =Max., V _{IN} =0.5V				±1	μA
I _{OZH}	Off State HIGH-Level Output Current	V _{CC} = Max., V _{OUT} = 2.7V				10	μA
I _{OZL}	Off State LOW-Level Output Current	V _{CC} = Max., V _{OUT} = 0.5V				−10	μA
I _{OS}	Output Short Circuit Current ^[7]	V _{CC} =Max., V _{OUT} =0.0V		−60	−120	−225	mA
I _{OFF}	Power-Off Disable	V _{CC} =0V, V _{OUT} =4.5V				±1	μA

Notes:

- H = HIGH Voltage Level. L = LOW Voltage Level X = Don't Care Z = HIGH Impedance = LOW-to-HIGH clock transition
- Unless otherwise noted, these limits are over the operating free-air temperature range.
- Unused inputs must always be connected to an appropriate logic voltage level, preferably either V_{CC} or ground.
- T_A is the "instant on" case temperature.
- Typical values are at V_{CC}=5.0V, T_A=+25°C ambient.
- This parameter is guaranteed but not tested.
- Not more than one output should be shorted at a time. Duration of short should not exceed one second. The use of high-speed test apparatus and/or sample and hold techniques are preferable in order to minimize internal chip heating and more accurately reflect operational values. Otherwise prolonged shorting of a high output may raise the chip temperature well above normal and thereby cause invalid readings in other parameters tests. In any sequence of parameter tests, I_{OS} tests should be performed last.

Capacitance^[2]

Parameter	Description	Typ. ^[5]	Max.	Unit
C _{IN}	Input Capacitance	5	10	pF
C _{OUT}	Output Capacitance	9	12	pF

Power Supply Characteristics

Parameter	Description	Test Conditions	Typ. ^[5]	Max.	Unit
I _{CC}	Quiescent Power Supply Current	V _{CC} =Max., V _{IN} ≤0.2V, V _{IN} ≥V _{CC} -0.2V	0.1	0.2	mA
ΔI _{CC}	Quiescent Power Supply Current (TTL inputs HIGH)	V _{CC} =Max., V _{IN} =3.4V, ^[8] f ₁ =0, Outputs Open	0.5	2.0	mA
I _{CCD}	Dynamic Power Supply Current ^[9]	V _{CC} =Max., One Bit Toggling, 50% Duty Cycle, Outputs Open, OE=GND, V _{IN} ≤0.2V or V _{IN} ≥V _{CC} -0.2V	0.06	0.12	mA/MHz
I _C	Total Power Supply Current ^[10]	V _{CC} =Max., f ₀ =10 MHz, 50% Duty Cycle, Outputs Open, One Bit Toggling at f ₁ =5 MHz, OE=GND, V _{IN} ≤0.2V or V _{IN} ≥V _{CC} -0.2V	0.7	1.4	mA
		V _{CC} =Max., f ₀ =10 MHz, 50% Duty Cycle, Outputs Open, One Bit Toggling at f ₁ =5 MHz, OE=GND, V _{IN} =3.4V or V _{IN} =GND	1.2	3.4	mA
		V _{CC} =Max., f ₀ =10 MHz, 50% Duty Cycle, Outputs Open, Eight Bits Toggling at f ₁ =2.5 MHz, OE=GND, V _{IN} ≤0.2V or V _{IN} ≥V _{CC} -0.2V	1.6	3.2 ^[11]	mA
		V _{CC} =Max., f ₀ =10 MHz, 50% Duty Cycle, Outputs Open, Eight Bits Toggling at f ₁ =2.5 MHz, OE=GND, V _{IN} =3.4V or V _{IN} =GND	3.9	12.2 ^[11]	mA

Notes:

8. Per TTL driven input (V_{IN}=3.4V); all other inputs at V_{CC} or GND.
9. This parameter is not directly testable, but is derived for use in Total Power Supply calculations.
10. I_C = I_{QUIESCENT} + I_{INPUTS} + I_{DYNAMIC}
I_C = I_{CC} + ΔI_{CC}D_HN_T + I_{CCD}(f₀/2 + f₁N₁)
I_{CC} = Quiescent Current with CMOS input levels
ΔI_{CC} = Power Supply Current for a TTL HIGH input (V_{IN}=3.4V)
D_H = Duty Cycle for TTL inputs HIGH
N_T = Number of TTL inputs at D_H
I_{CCD} = Dynamic Current caused by an input transition pair (HLH or LHL)
f₀ = Clock frequency for registered devices, otherwise zero
f₁ = Input signal frequency
N₁ = Number of inputs changing at f₁
All currents are in milliamps and all frequencies are in megahertz.
11. Values for these conditions are examples of the I_{CC} formula. These limits are guaranteed but not tested.

Switching Characteristics^[12] Over the Operating Range

Parameter	Description	FCT374T/FCT574T				FCT374AT/FCT574AT				Unit	Fig. No. ^[13]
		Military		Commercial		Military		Commercial			
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.		
t _{PLH} t _{PHL}	Propagation Delay Clock to Output	2.0	11.0	2.0	10.0	2.0	7.2	2.0	6.5	ns	1, 5
t _{PZH} t _{PZL}	Output Enable Time	1.5	14.0	1.5	12.5	1.5	7.5	1.5	6.5	ns	1, 7, 8
t _{PHZ} t _{PLZ}	Output Disable Time	1.5	8.0	1.5	8.0	1.5	6.5	1.5	5.5	ns	1, 7, 8
t _S	Set–Up Time HIGH or LOW D to CP	2.0		2.0		2.0		2.0		ns	4
t _H	Hold Time HIGH or LOW D to CP	1.5		1.5		1.5		1.5		ns	4
t _W	Clock Pulse Width ^[14] HIGH or LOW	7.0		7.0		6.0		5.0		ns	5

Parameter	Description	FCT374CT/FCT574CT				FCT374DT/ FCT574DT		Unit	Fig. No. ^[13]
		Military		Commercial		Commercial			
		Min.	Max.	Min.	Max.	Min.	Max.		
t _{PLH} t _{PHL}	Propagation Delay Clock to Output	2.0	6.2	2.0	5.2	2.0	4.2	ns	1, 5
t _{PZH} t _{PZL}	Output Enable Time	1.5	6.2	1.5	5.5	1.5	4.8	ns	1, 7, 8
t _{PHZ} t _{PLZ}	Output Disable Time	1.5	5.7	1.5	5.0	1.5	4.0	ns	1, 7, 8
t _S	Set-Up Time, HIGH or LOW D to CP	2.0		2.0		2.0		ns	4
t _H	Hold Time, HIGH or LOW D to CP	1.5		1.5		1.5		ns	4
t _W	Clock Pulse Width ^[14] HIGH or LOW	6.0		5.0		3.0		ns	5

Shaded areas contain preliminary information.

Notes:

12. Minimum limits are guaranteed but not tested on Propagation Delays.
13. See "Parameter Measurement Information" in the General Information section.
14. With one data channel toggling, t_{W(L)}=t_{W(H)}=4.0 ns and t_r=t_f=1.0 ns.



Ordering Information—FCT374T

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
4.2	CY74FCT374DTQC	Q5	20-Lead (150-Mil) QSOP	Commercial
	CY74FCT374DTSOC	S5	20-Lead (300-Mil) Molded SOIC	
5.2	CY74FCT374CTQC	Q5	20-Lead (150-Mil) QSOP	Commercial
	CY74FCT374CTSOC	S5	20-Lead (300-Mil) Molded SOIC	
6.2	CY54FCT374CTDMB	D6	20-Lead (300-Mil) CerDIP	Military
	CY54FCT374CTLMB	L61	20-Pin Square Leadless Chip Carrier	
6.5	CY74FCT374ATPC	P5	20-Lead (300-Mil) Molded DIP	Commercial
	CY74FCT374ATQC	Q5	20-Lead (150-Mil) QSOP	
	CY74FCT374ATSOC	S5	20-Lead (300-Mil) Molded SOIC	
7.2	CY54FCT374ATLMB	L61	20-Pin Square Leadless Chip Carrier	Military
10.0	CY74FCT374TQC	Q5	20-Lead (150-Mil) QSOP	Commercial
	CY74FCT374TSOC	S5	20-Lead (300-Mil) Molded SOIC	
11.0	CY54FCT374TDMB	D6	20-Lead (300-Mil) CerDIP	Military
	CY54FCT374TLMB	L61	20-Pin Square Leadless Chip Carrier-	

Ordering Information—FCT574T

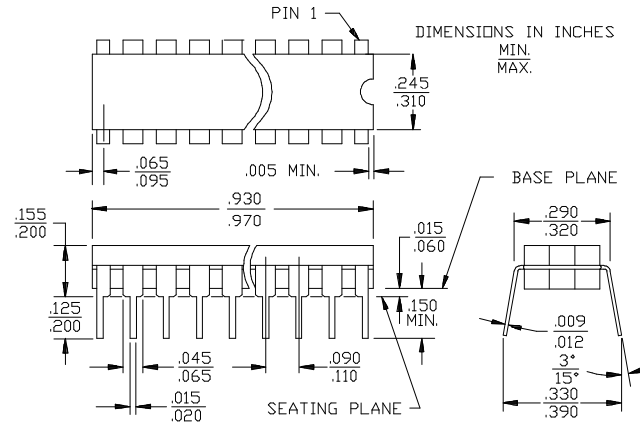
Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
4.2	CY74FCT574DTQC	Q5	20-Lead (150-Mil) QSOP	Commercial
	CY74FCT574DTSOC	S5	20-Lead (300-Mil) Molded SOIC	
5.2	CY74FCT574CTQC	Q5	20-Lead (150-Mil) QSOP	Commercial
	CY74FCT574CTSOC	S5	20-Lead (300-Mil) Molded SOIC	
6.2	CY54FCT574CTDMB	D6	20-Lead (300-Mil) CerDIP	Military
6.5	CY74FCT574ATPC	P5	20-Lead (300-Mil) Molded DIP	Commercial
	CY74FCT574ATQC	Q5	20-Lead (150-Mil) QSOP	
	CY74FCT574ATSOC	S5	20-Lead (300-Mil) Molded SOIC	
7.2	CY54FCT574ATDMB	D6	20-Lead (300-Mil) CerDIP	Military
10.0	CY74FCT574TQC	Q5	20-Lead (150-Mil) QSOP	Commercial
	CY74FCT574TSOC	S5	20-Lead (300-Mil) Molded SOIC	
11.0	CY54FCT574TDMB	D6	20-Lead (300-Mil) CerDIP	Military

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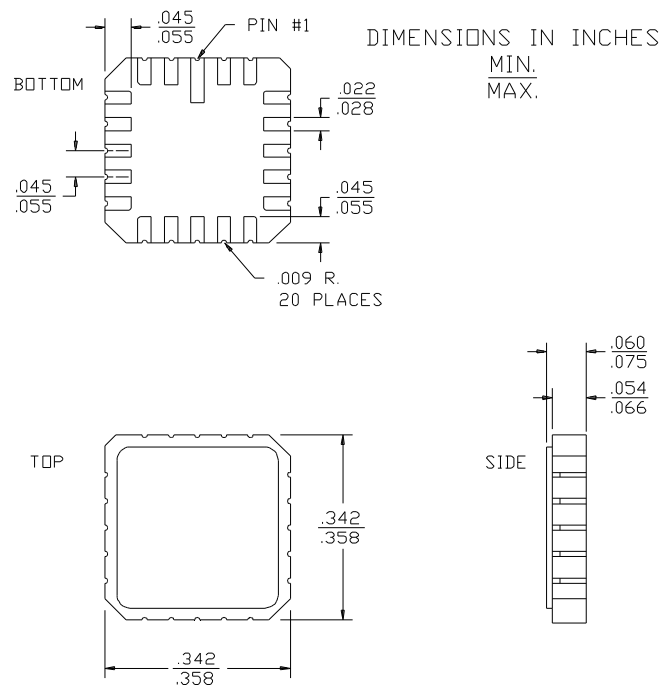
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Package Diagrams

20-Lead (300-Mil) CerDIP D6
MIL-STD-1835 D-8Config.A

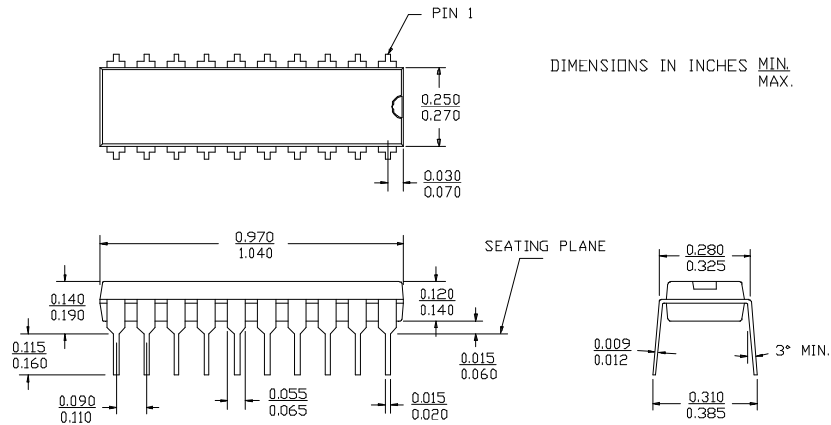


20-Pin Square Leadless Chip Carrier L61
MIL-STD-1835 C-2A

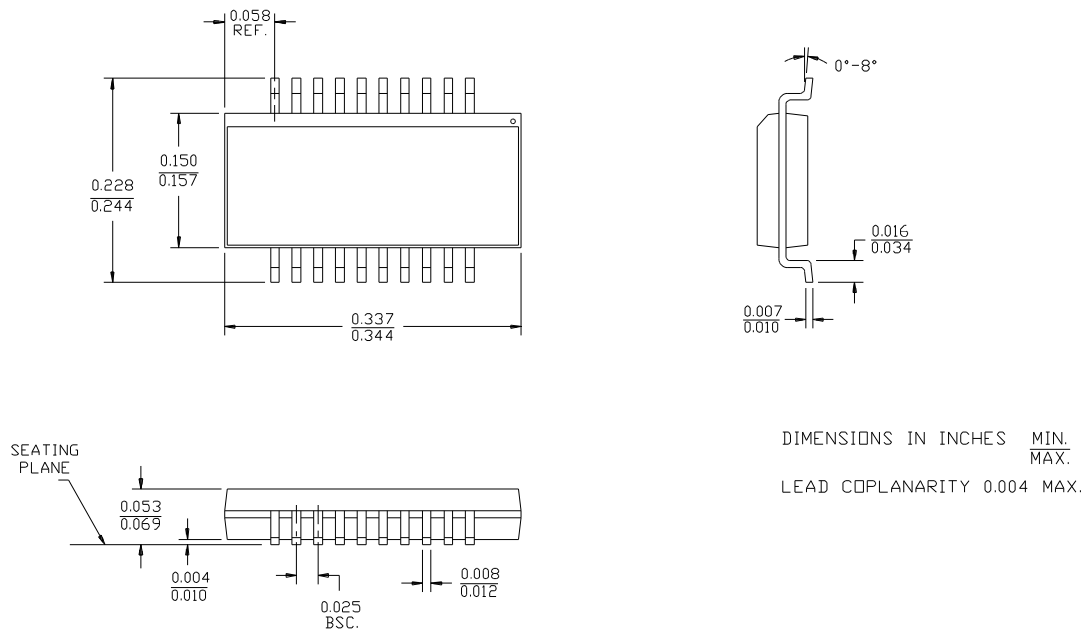


Package Diagrams (continued)

20-Lead (300-Mil) Molded DIP P5



20-Lead Quarter Size Outline Q5





Package Diagrams (continued)

20-Lead (300-Mil) Molded SOIC S5

